

$^{30}\text{Si}({}^{16}\text{O},\text{pny}) \quad 1975\text{Ch37}$

| Type | Author | Citation | Literature Cutoff Date |
|-----------------|---------------------------|------------------|------------------------|
| Full Evaluation | Jun Chen and Balraj Singh | NDS 190,1 (2023) | 20-Jun-2023 |

1975Ch37: E=30 MeV ${}^{16}\text{O}$ beam produced from the MP tandem Van de Graaff accelerator. Targets of metallic Si (enriched to 95% in ${}^{30}\text{Si}$) on gold backings. Ge(Li) detectors for detecting γ -rays. Measured $E\gamma$, $\gamma(t)$, perturbed $\gamma(\theta)$. Deduced $T_{1/2}$, g factors for the levels of 235 and 350 keV.

 ^{44}Sc Levels

g factor is measured using the time integral perturbed angular distribution technique (TIPAD) with an external fields ([1975Ch37](#)).

| E(level) | J^π [†] | $T_{1/2}$ [‡] | Comments |
|----------|----------------------|------------------------|--|
| 0 | 2 ⁺ | | |
| 235 | 2 ⁻ | 6.12 ns 23 | $g=0.30$ I3 (1975Ch37) |
| 350 | 4 ⁺ | 3.13 ns 19 | $g=0.90$ I2 (1975Ch37) |

[†] From the Adopted Levels.

[‡] From $\gamma(t)$ ([1975Ch37](#)).

 $\gamma(^{44}\text{Sc})$

| E γ | E i (level) | J_i^π | E f | J_f^π |
|------------|---------------|----------------|-------|----------------|
| 235 | 235 | 2 ⁻ | 0 | 2 ⁺ |
| 350 | 350 | 4 ⁺ | 0 | 2 ⁺ |

 $^{30}\text{Si}({}^{16}\text{O},\text{pny}) \quad 1975\text{Ch37}$ Level Scheme